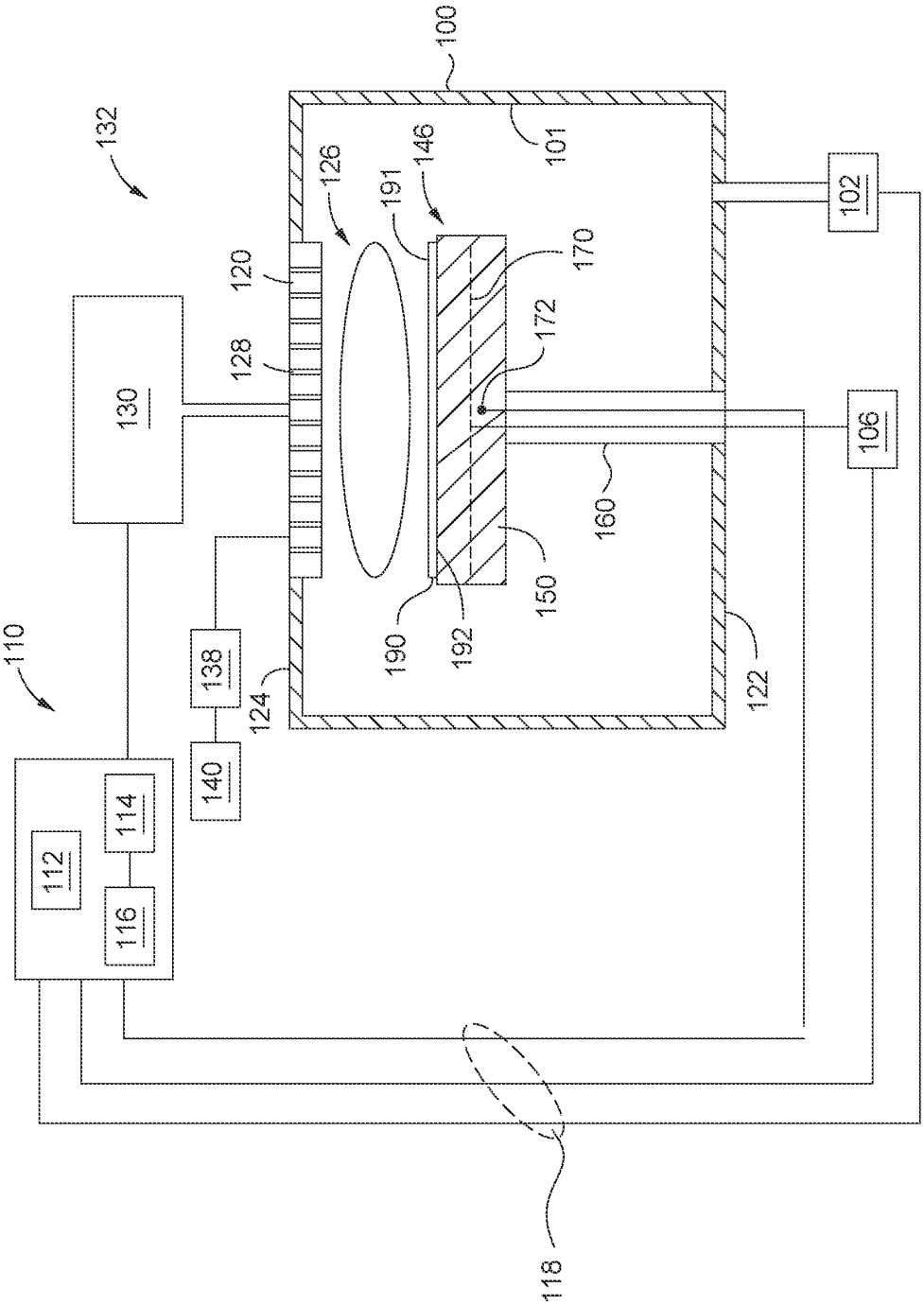

100
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FIG. 1A

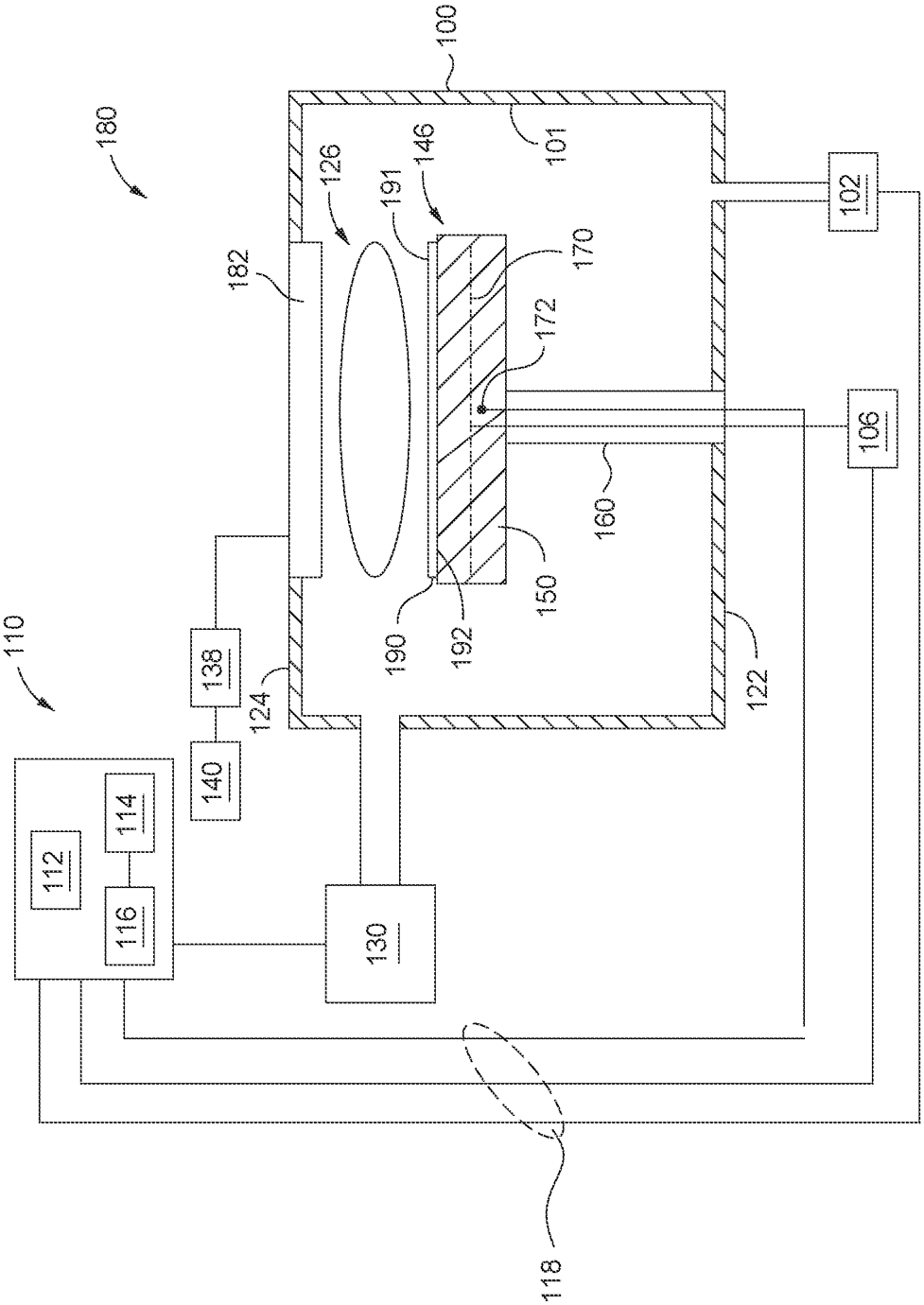

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126
146
191
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192
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124
122
140
114
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116
130
118

FIG. 1B

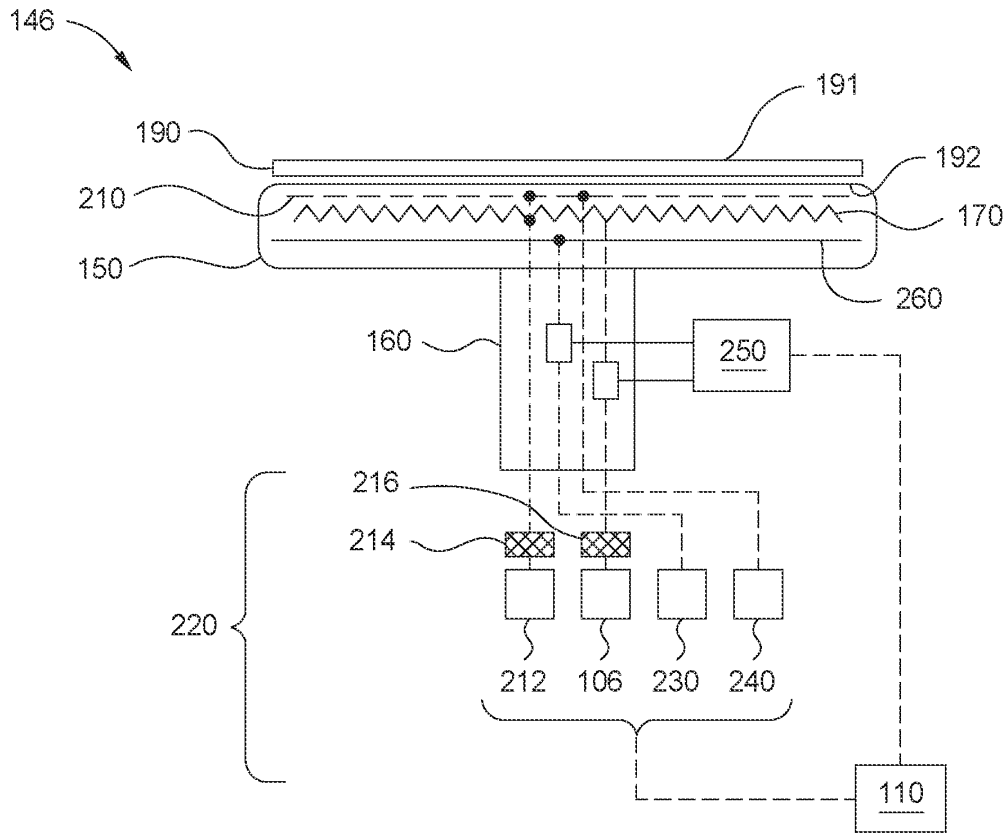

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191
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110

FIG. 2

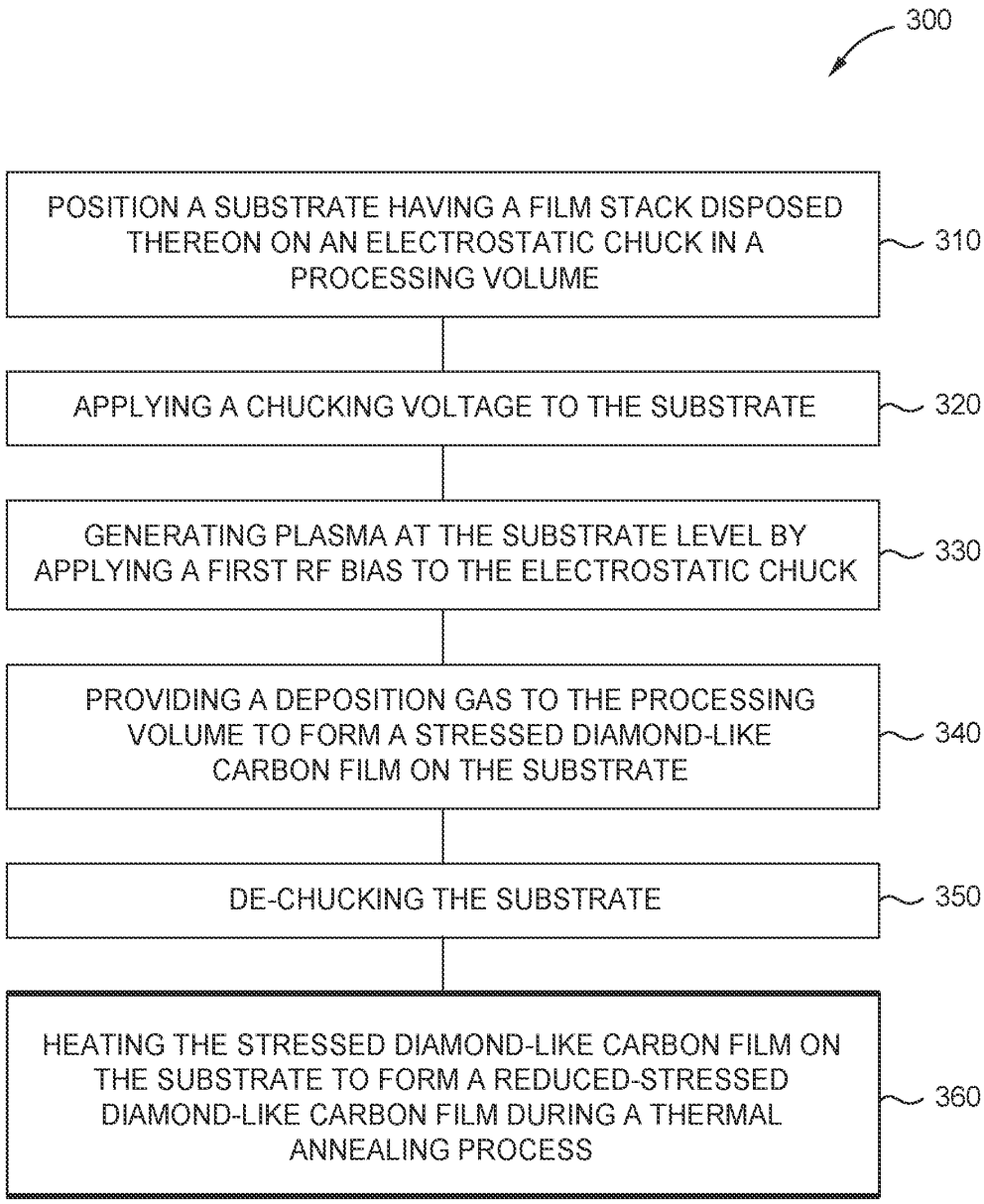

300
POSITION A SUBSTRATE HAVING A FILM STACK DISPOSED THEREON ON AN ELECTROSTATIC CHUCK IN A PROCESSING VOLUME
310
APPLYING A CHUCKING VOLTAGE TO THE SUBSTRATE
320
GENERATING PLASMA AT THE SUBSTRATE LEVEL BY APPLYING A FIRST RF BIAS TO THE ELECTROSTATIC CHUCK
330
PROVIDING A DEPOSITION GAS TO THE PROCESSING VOLUME TO FORM A STRESSED DIAMOND-LIKE CARBON FILM ON THE SUBSTRATE
340
DE-CHUCKING THE SUBSTRATE
350
HEATING THE STRESSED DIAMOND-LIKE CARBON FILM ON THE SUBSTRATE TO FORM A REDUCED-STRESSED DIAMOND-LIKE CARBON FILM DURING A THERMAL ANNEALING PROCESS
360

FIG. 3

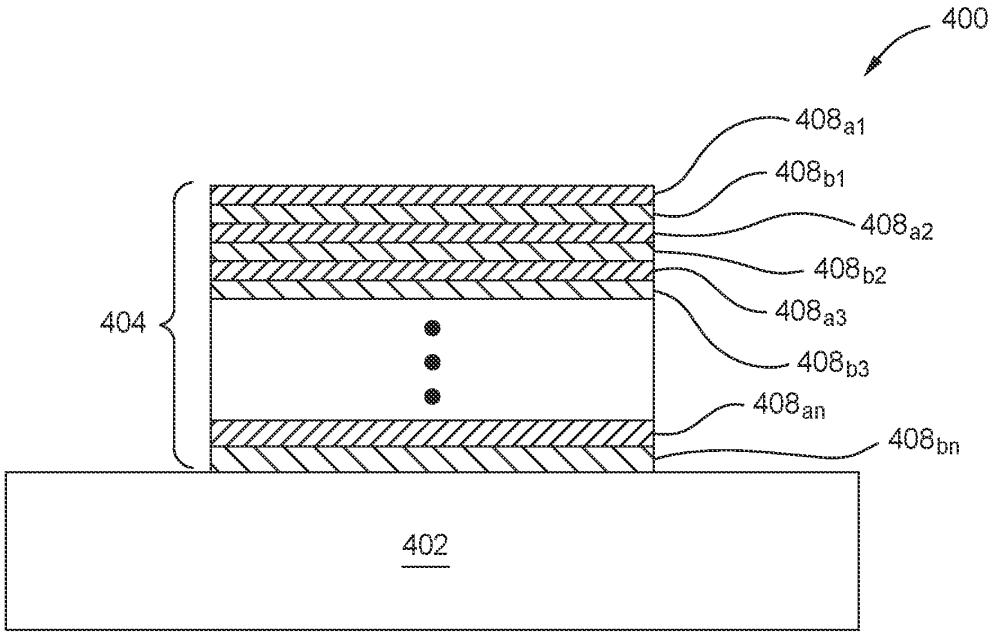

400
408_{a1}
408_{b1}
408_{a2}
408_{b2}
408_{a3}
408_{b3}
408_{an}
408_{bn}
404
402

FIG. 4A

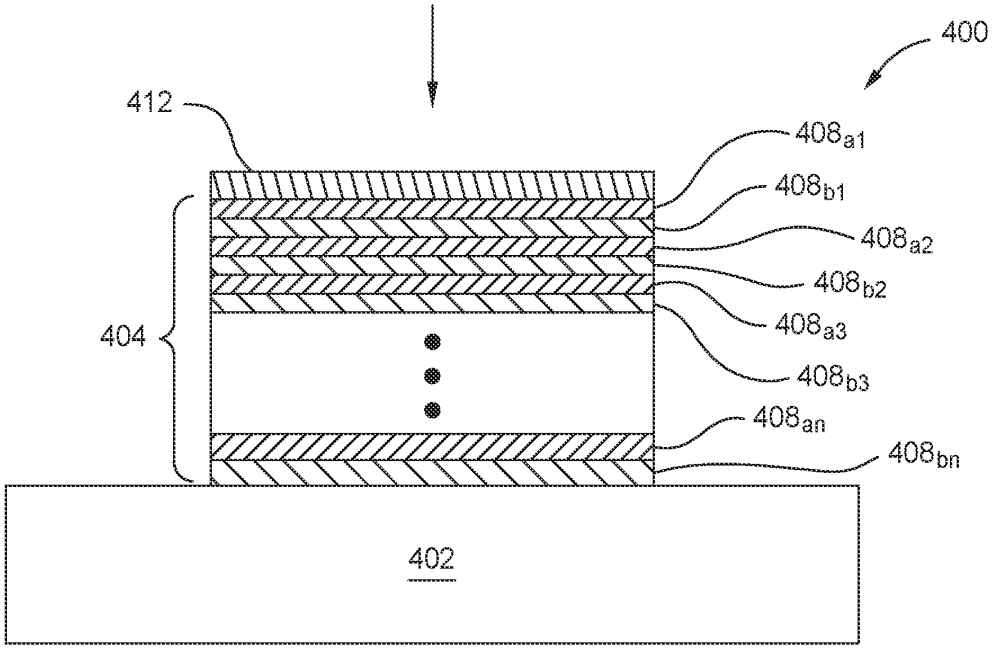

400
412
408_{a1}
408_{b1}
408_{a2}
408_{b2}
408_{a3}
408_{b3}
408_{an}
408_{bn}
404
402

FIG. 4B

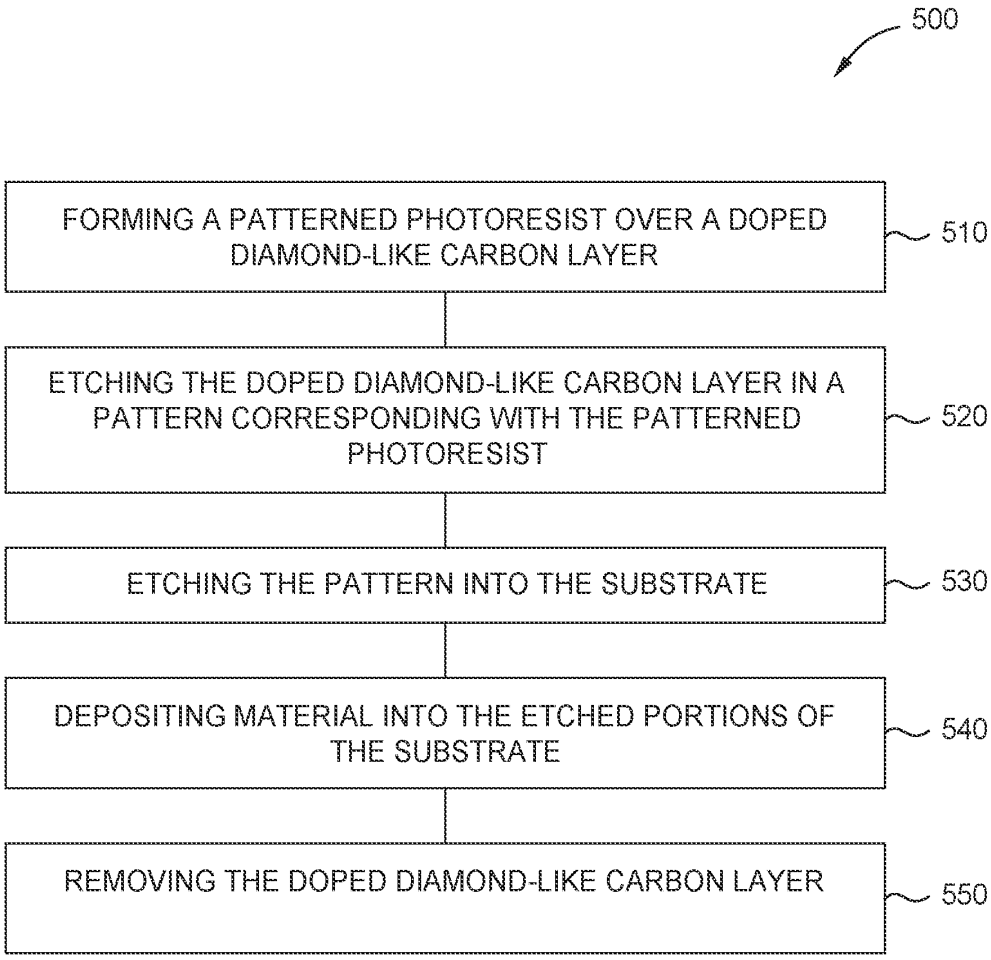

500
FORMING A PATTERNED PHOTORESIST OVER A DOPED DIAMOND-LIKE CARBON LAYER
510
ETCHING THE DOPED DIAMOND-LIKE CARBON LAYER IN A PATTERN CORRESPONDING WITH THE PATTERNED PHOTORESIST
520
ETCHING THE PATTERN INTO THE SUBSTRATE
530
DEPOSITING MATERIAL INTO THE ETCHED PORTIONS OF THE SUBSTRATE
540
REMOVING THE DOPED DIAMOND-LIKE CARBON LAYER
550

FIG. 5